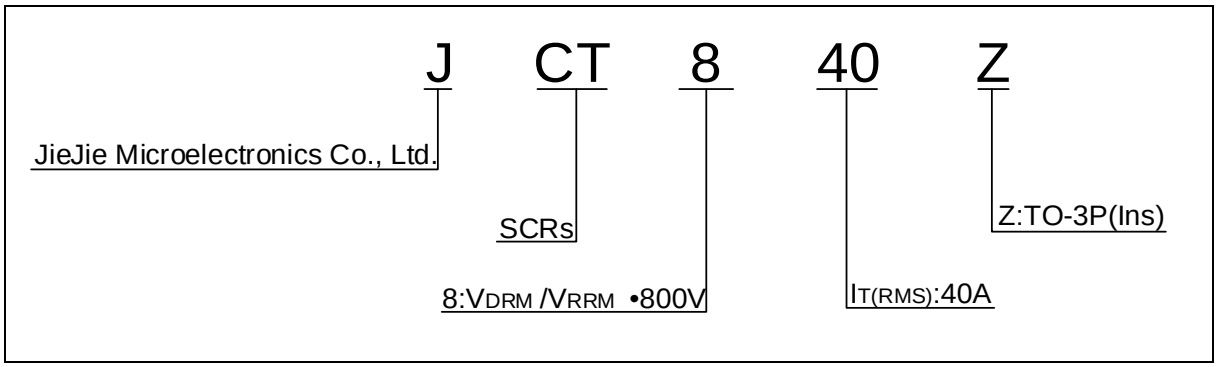
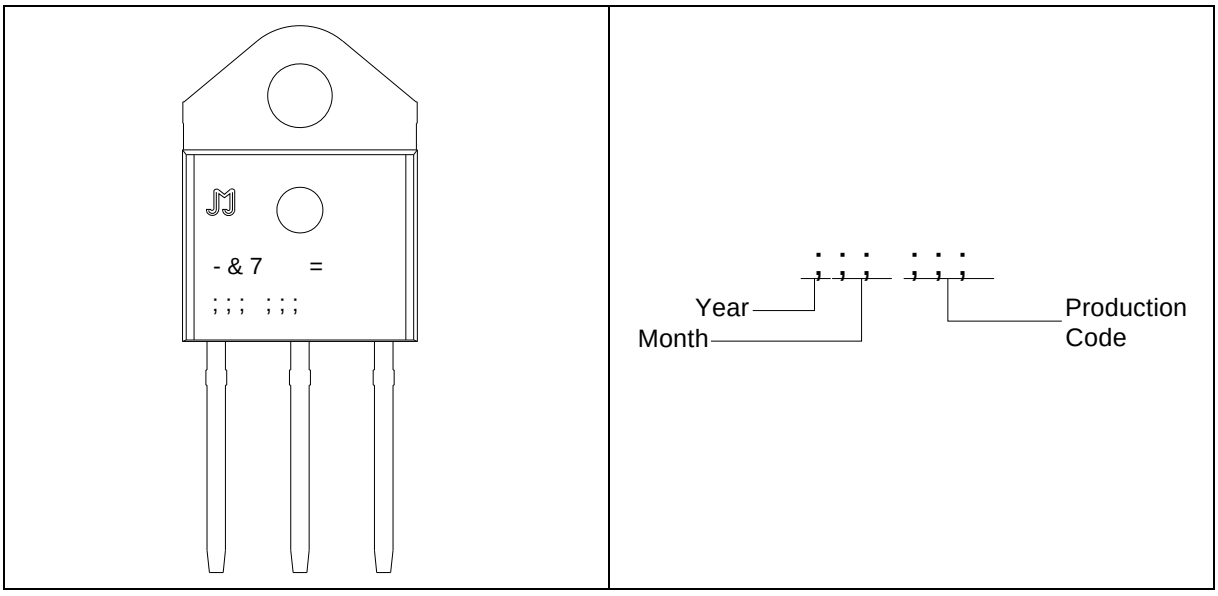
Peak gate current (t_p=20μs , T_j=125)	I_{GM}	10	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage			
T_j			


J
CT
8
40
Z
JieJie Microelectronics Co., Ltd.
SCRs
8:VDRM /VRRM •800V
IT(RMS):40A
Z:TO-3P(Ins)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Code

FIG.1: Maximum power dissipation versus RMS on-state current

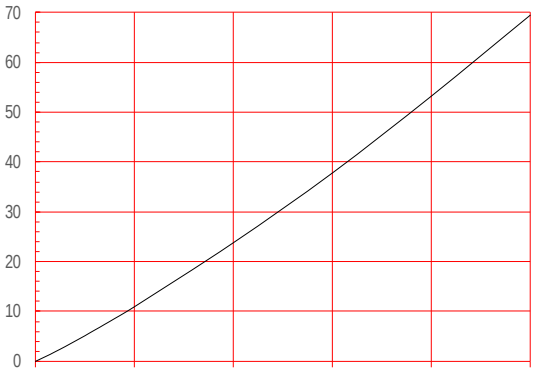
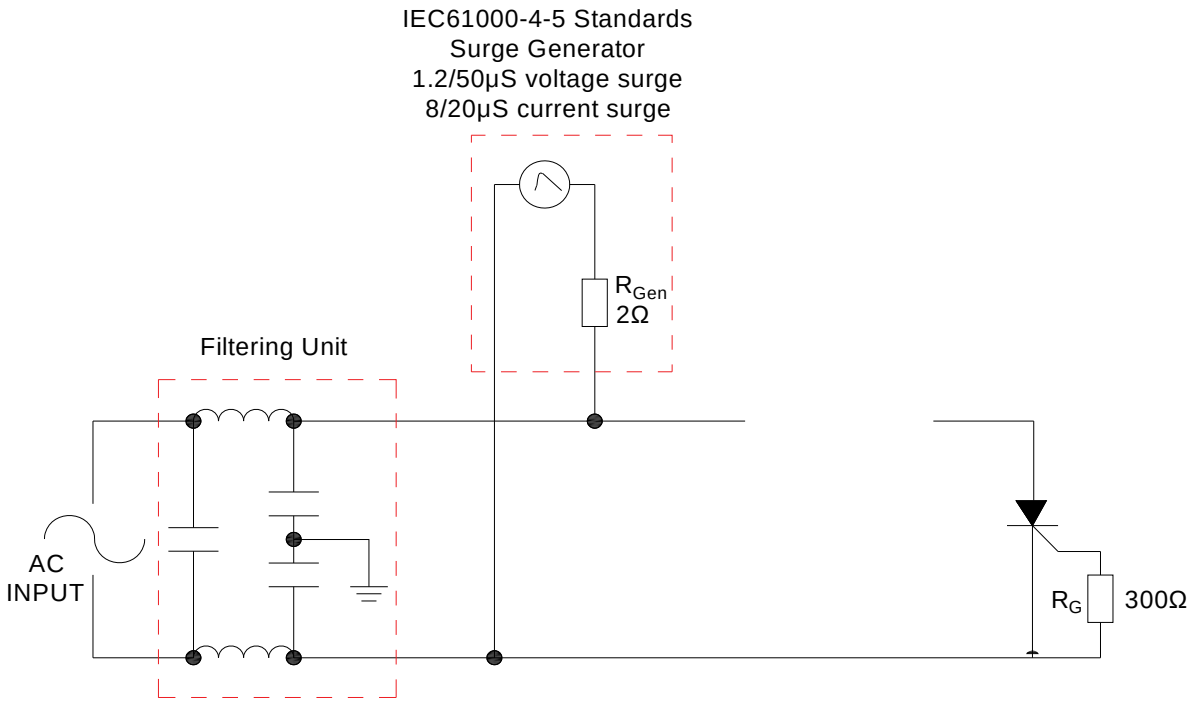


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT840Z	800	35	TO-3P(Ins)	30	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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